

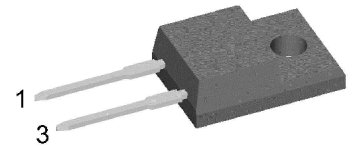
# HiPerFRED

$V_{RRM}$	=	600 V
$I_{FAV}$	=	15 A
$t_{rr}$	=	25 ns

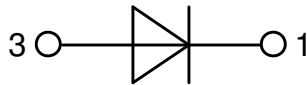
High Performance Fast Recovery Diode  
 Low Loss and Soft Recovery  
 Single Diode

Part number

**DPG30I600PM**



Backside: isolated



### Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low  $I_{rm}$ -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low  $I_{rm}$  reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

### Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

### Package: TO-220FP

- Isolation Voltage: 2500 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

### Disclaimer Notice

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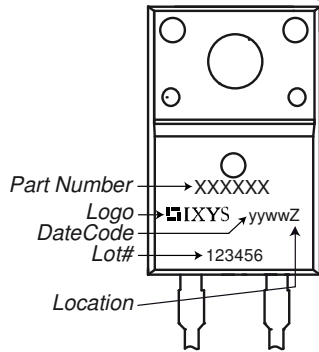


Fast Diode				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM}$	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			600	V	
$V_{RRM}$	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			600	V	
$I_R$	reverse current, drain current	$V_R = 600 V$	$T_{VJ} = 25^{\circ}C$		250	$\mu A$	
		$V_R = 600 V$	$T_{VJ} = 150^{\circ}C$		2	mA	
$V_F$	forward voltage drop	$I_F = 30 A$	$T_{VJ} = 25^{\circ}C$		2,52	V	
		$I_F = 60 A$			3,22	V	
		$I_F = 30 A$	$T_{VJ} = 150^{\circ}C$		1,63	V	
		$I_F = 60 A$			2,27	V	
$I_{FAV}$	average forward current	$T_C = 95^{\circ}C$ rectangular $d = 0.5$	$T_{VJ} = 175^{\circ}C$		15	A	
$V_{FO}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 175^{\circ}C$		0,84	V	
$r_F$	slope resistance				20	m $\Omega$	
$R_{thJC}$	thermal resistance junction to case				3,5	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0,5		K/W	
$P_{tot}$	total power dissipation		$T_C = 25^{\circ}C$		165	W	
$I_{FSM}$	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}; V_R = 0 V$	$T_{VJ} = 45^{\circ}C$		250	A	
$C_J$	junction capacitance	$V_R = 400 V$ $f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		26	pF	
$I_{RM}$	max. reverse recovery current	} $I_F = 30 A; V_R = 300 V$ $-di_F/dt = 200 A/\mu s$	$T_{VJ} = 25^{\circ}C$		2,5	A	
$t_{rr}$	reverse recovery time		$T_{VJ} = 100^{\circ}C$		4,5	A	
			$T_{VJ} = 25^{\circ}C$		25	ns	
			$T_{VJ} = 100^{\circ}C$		70	ns	



Package TO-220FP		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			35	A
$T_{VJ}$	virtual junction temperature		-55		175	°C
$T_{op}$	operation temperature		-55		150	°C
$T_{stg}$	storage temperature		-55		150	°C
<b>Weight</b>				2		g
$M_D$	mounting torque		0,4		0,6	Nm
$F_C$	mounting force with clip		20		60	N
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	3,2	2,7		mm
$d_{Spb/Apb}$		terminal to backside	2,5	2,5		mm
$V_{ISOL}$	isolation voltage	t = 1 second	2500			V
		t = 1 minute	2100			V

**Product Marking**



**Part description**

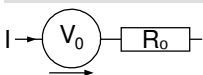
- D = Diode
- P = HiPerFRED
- G = extreme fast
- 30 = Current Rating [A]
- I = Single Diode
- 600 = Reverse Voltage [V]
- PM = TO-220ACFP (2)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DPG30I600PM	DPG30I600PM	Tube	50	521763

**Equivalent Circuits for Simulation**

\* on die level

$T_{VJ} = 175^{\circ}C$

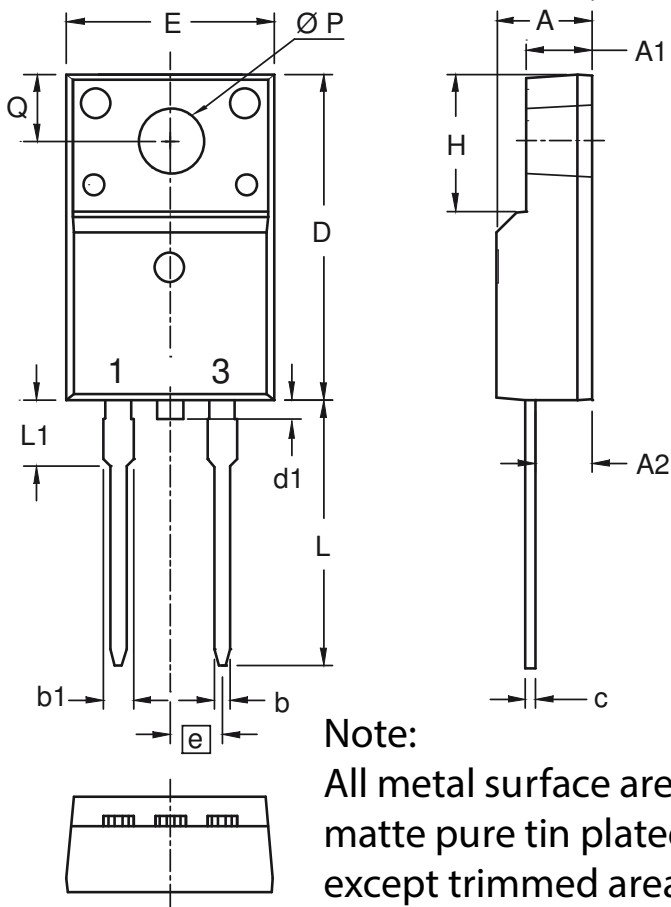


**Fast Diode**

$V_{0\ max}$	threshold voltage	0,84	V
$R_{0\ max}$	slope resistance *	17	mΩ



**Outlines TO-220FP**



Dim.	Millimeters		Inches	
	min	max	min	max
A	4.50	4.90	0.177	0.193
A1	2.34	2.74	0.092	0.108
A2	2.56	2.96	0.101	0.117
b	0.70	0.90	0.028	0.035
b1	1.27	1.47	0.050	0.058
c	0.45	0.60	0.018	0.024
D	15.67	16.07	0.617	0.633
d1	0	1.10	0	0.043
E	9.96	10.36	0.392	0.408
e	2.54 BSC		0.100 BSC	
H	6.48	6.88	0.255	0.271
L	12.68	13.28	0.499	0.523
L1	3.03	3.43	0.119	0.135
ØP	3.08	3.28	0.121	0.129
Q	3.20	3.40	0.126	0.134



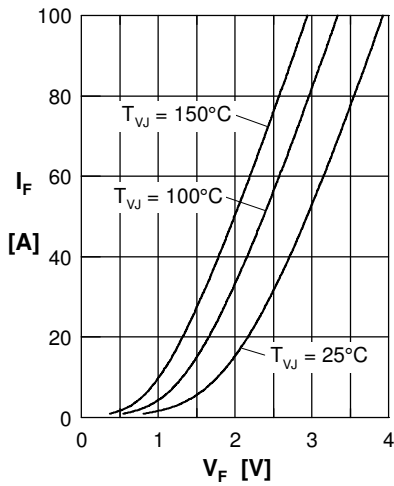
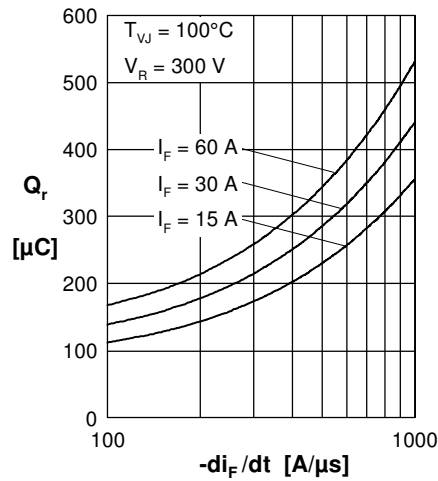
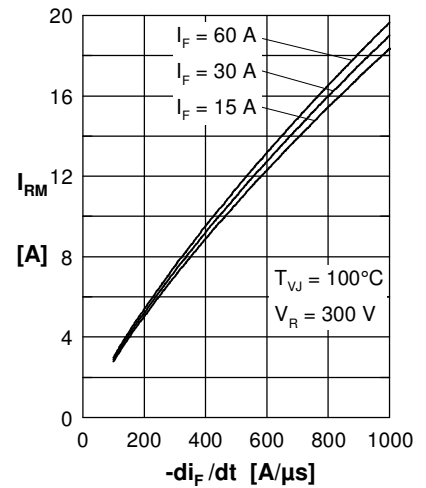
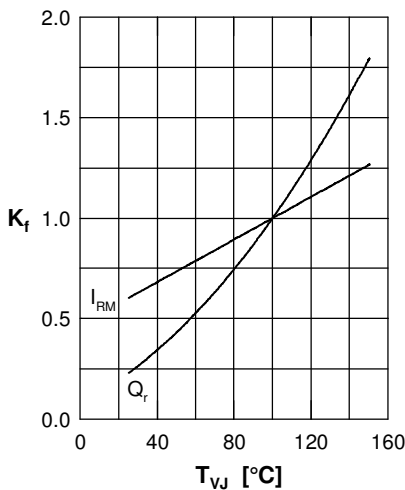
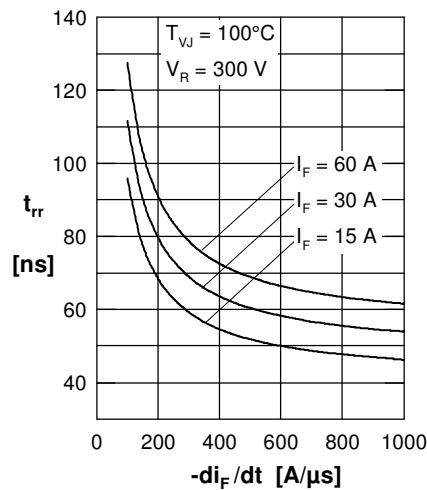
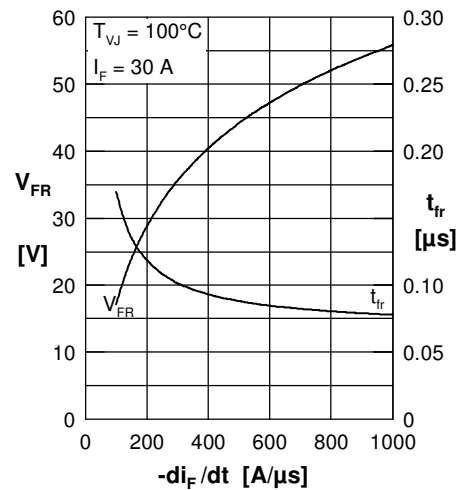
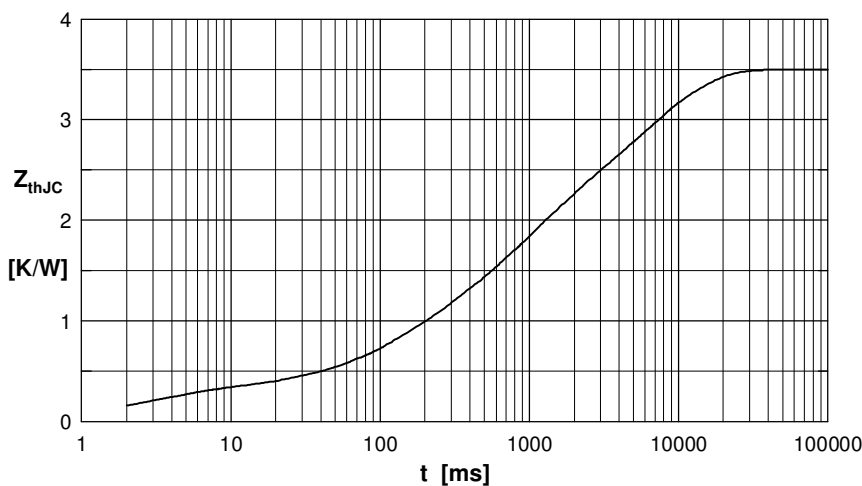
**Fast Diode**

 Fig. 1 Forward current  $I_F$  versus  $V_F$ 

 Fig. 2 Typ. reverse recovery charge  $Q_r$  versus  $-di_F/dt$ 

 Fig. 3 Typ. peak reverse current  $I_{RM}$  versus  $-di_F/dt$ 

 Fig. 4 Dynamic parameters  $K_r$ ,  $I_{RM}$  versus  $T_{VJ}$ 

 Fig. 5 Typ. recovery time  $t_{tr}$  versus  $-di_F/dt$ 

 Fig. 6 Typ. peak forward voltage  $V_{FR}$  and  $t_{tr}$  versus  $di_F/dt$ 


Fig. 7 Transient thermal impedance junction to case

 Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.30	0.003
2	0.50	0.130
3	1.15	0.800
4	1.55	6.500